

March 2012 SuperFET[®] II

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FCP380N60 / FCPF380N60 N-Channel MOSFET

FCP380N60 / FCPF380N60 600V N-Channel MOSFET

Features

- 650V @T_J = 150°C
- Max. R_{DS(on)} = 380mΩ
- Ultra low gate charge (typ. Q_g = 30nC)
- Low effective output capacitance (typ. C_{oss} .eff = 95pF)
- 100% avalanche tested

Description

SuperFET[®]II is, Fairchild's proprietary, new generation of high voltage MOSFET family that is utilizing an advanced charge balance mechanism for outstanding low on-resistance and lower gate charge performance.

This advanced technology has been tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate and higher avalanche energy. Consequently, SuperFET[®]II is very suitable for various AC/DC power conversion in switching mode operation for system miniaturization and higher efficiency.



Absolute Maximum Ratings $T_C = 25^{\circ}C$ unless otherwise noted

Symbol		Parameter		FCP380N60	FCPF380N60	Units
V _{DSS}	Drain to Source Voltage			6	00	V
N/	Cata ta Sauraa Maltaga	-DC		±	20	V
Gate to Source Voltage		-AC	(f>1HZ)	±	30	v
L Drain Current		-Continuous (T _C = 25 ^o C)		10.2	10.2*	^
D	Drain Current	-Continuous (T _C = 100 ^o C)		6.4	6.4*	A
I _{DM}	Drain Current	- Pulsed	(Note 1)	30.6	30.6*	А
E _{AS}	Single Pulsed Avalanche Energy (Note 2)		211.6		mJ	
I _{AR}	Avalanche Current		(Note 1)) 2.3		А
E _{AR}	Repetitive Avalanche Energy		(Note 1)) 1.06		mJ
dv/dt	Peak Diode Recovery dv/dt		(Note 3)) 20		V/ns
uv/ui	MOSFET dv/dt			100		v/ns
D	Dower Dissinction	(T _C = 25°C)		106	31	W
PD	Power Dissipation - Derate above 25°C		0.85	0.25	W/ºC	
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to	o +150	°C	
TL		Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds		3	00	°C

*Drain current limited by maximum junction temperature

Thermal Characteristics

Symbol	Parameter F		FCPF380N60	Units
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction to Case	1.18	4	
$R_{\theta CS}$	Thermal Resistance, Case to Heat Sink (Typical)	0.5	0.5	°C/W
R_{\thetaJA}	Thermal Resistance, Junction to Ambient	62.5	62.5	

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Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FCP380N60	FCP380N60	TO-220	-	-	50
FCPF380N60	FCPF380N60	TO-220F	-	-	50

Electrical Characteristics T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
Off Charac	cteristics					
	Drain to Source Breakdown Maltage	V _{GS} = 0V, I _D = 10mA, T _J = 25°C	600	-	-	V
BV _{DSS} Drain to Source Breakdown Voltage	V _{GS} = 0V, I _D = 10mA, T _J = 150°C	650	-	-	V	
$\frac{\Delta BV_{DSS}}{\Delta T_{,l}}$	Breakdown Voltage Temperature Coefficient	I_D = 10mA, Referenced to 25°C	-	0.6	-	V/ºC
BV _{DS}	Drain-Source Avalanche Breakdown Voltage	V _{GS} = 0V, I _D = 10A	-	700	-	V
1	Zoro Cata Voltago Drain Current	V _{DS} = 480V, V _{GS} = 0V	-	-	1	
IDSS Ze	Zero Gate Voltage Drain Current	V _{DS} = 480V, T _C = 125 ^o C	-	-	10	μA
I _{GSS}	Gate to Body Leakage Current	V_{GS} = ±20V, V_{DS} = 0V	-	-	±100	nA

On Characteristics

V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	2.5	-	3.5	V
R _{DS(on)}	Static Drain to Source On Resistance	V _{GS} = 10V, I _D = 5A	-	0.33	0.38	Ω
9 _{FS}	Forward Transconductance	$V_{DS} = 20V, I_{D} = 5A$	-	11	-	S

Dynamic Characteristics

C _{iss}	Input Capacitance		-	1250	1665	pF
C _{oss}	Output Capacitance	$V_{DS} = 25V, V_{GS} = 0V$		905	1205	pF
C _{rss}	Reverse Transfer Capacitance	1 = 10012	-	45	60	pF
C _{oss}	Output Capacitance	V _{DS} = 380V, V _{GS} = 0V, f = 1.0MHz	-	23	-	pF
C _{oss} eff.	Effective Output Capacitance	V_{DS} = 0V to 480V, V_{GS} = 0V	-	95	-	pF
Q _{g(tot)}	Total Gate Charge at 10V	V _{DS} = 380V, I _D = 5A	-	30	40	nC
Q _{gs}	Gate to Source Gate Charge	V _{GS} = 10V	-	5	-	nC
Q _{gd}	Gate to Drain "Miller" Charge	(Note 4)	-	10	-	nC
EŠR	Equivalent Series Resistance	Drain Open		1		Ω

Switching Characteristics

t _{d(on)}	Turn-On Delay Time		-	14	38	ns
t _r	Turn-On Rise Time	$V_{DD} = 380V, I_D = 5A$	-	7	24	ns
t _{d(off)}	Turn-Off Delay Time	V _{GS} = 10V, R = 4.7Ω	-	45	100	ns
t _f	Turn-Off Fall Time	(Note 4)	-	6	22	ns

Drain-Source Diode Characteristics

I _S	Maximum Continuous Drain to Source Dio	Maximum Continuous Drain to Source Diode Forward Current		-	10.2	Α
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	30.6	Α
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _{SD} = 5A	-	-	1.2	V
t _{rr}	Reverse Recovery Time	$V_{GS} = 0V, I_{SD} = 5A$	-	240	-	ns
Q _{rr}	Reverse Recovery Charge	$dI_F/dt = 100A/\mu s$	-	2.7	-	μC

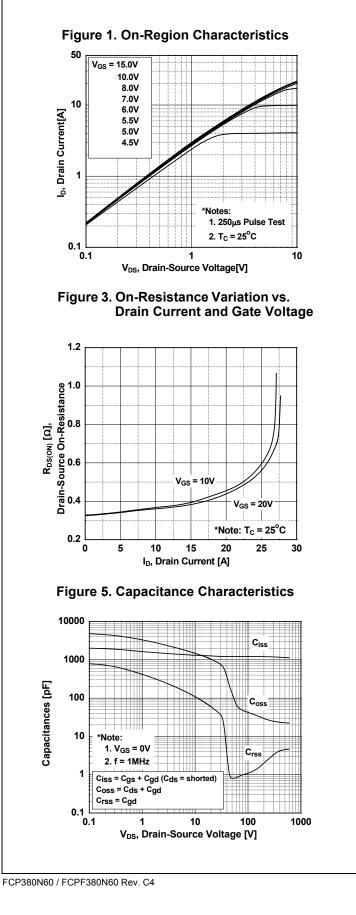
Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature

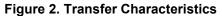
2. I_{AS} = 2.3A, V_{DD} = 50V, R_G = 25 Ω , Starting T_J = 25°C

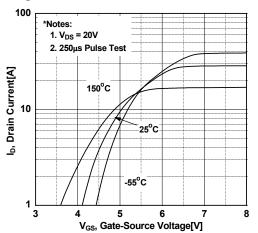
3. $I_{SD} \leq$ 5.1A, di/dt \leq 200A/µs, $V_{DD} \leq BV_{DSS},$ Starting T_J = 25°C

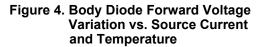
4. Essentially Independent of Operating Temperature Typical Characteristics



Typical Performance Characteristics







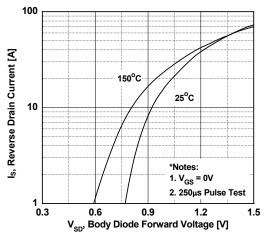
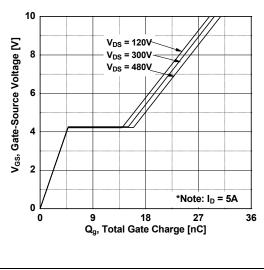
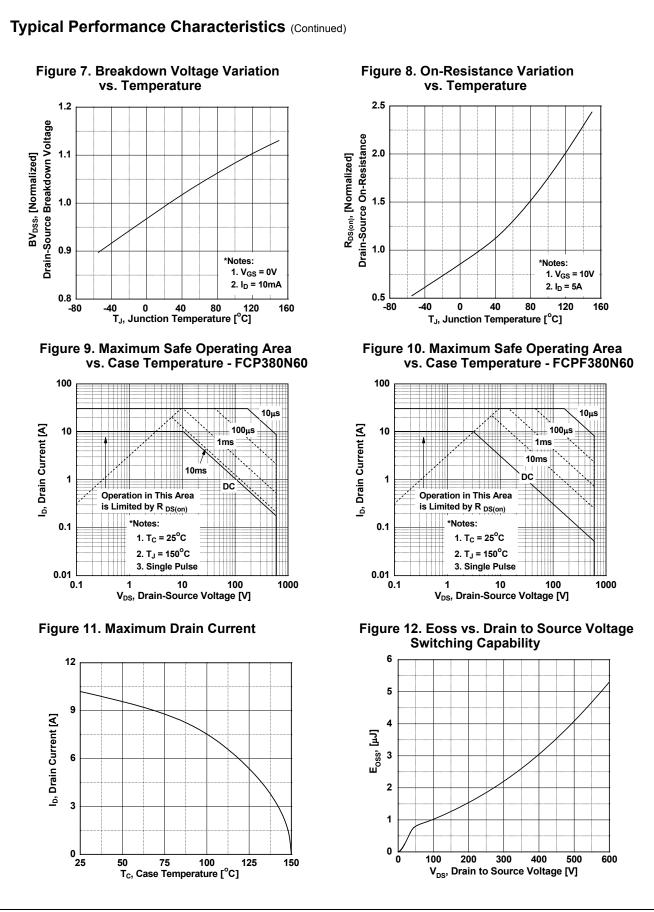
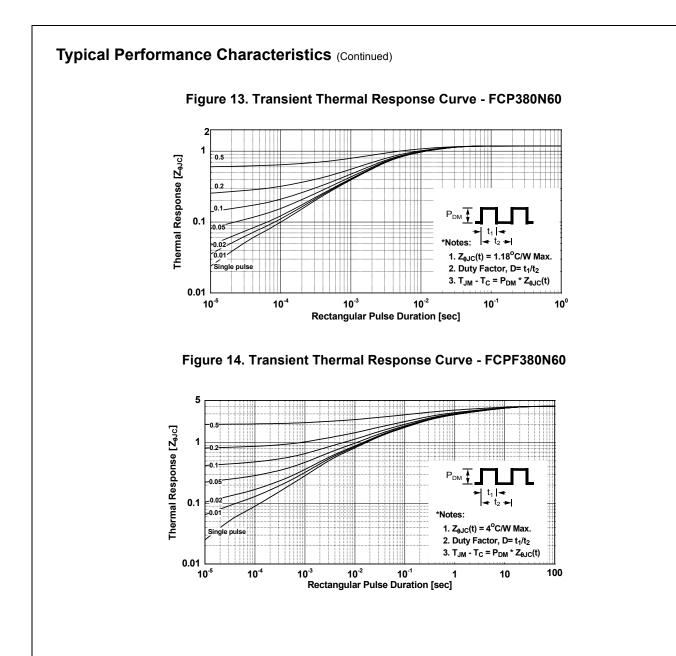


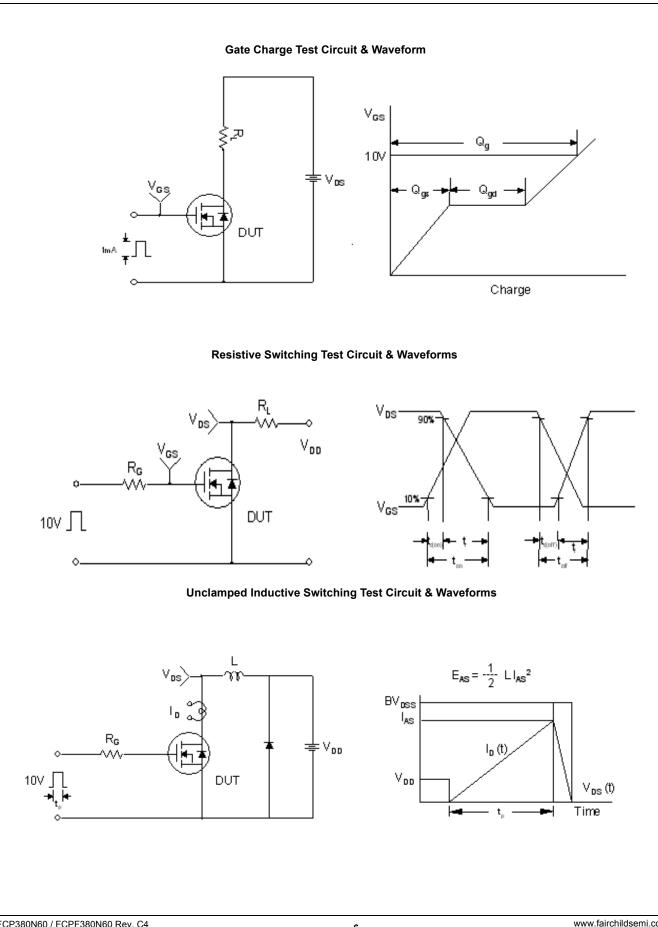
Figure 6. Gate Charge Characteristics



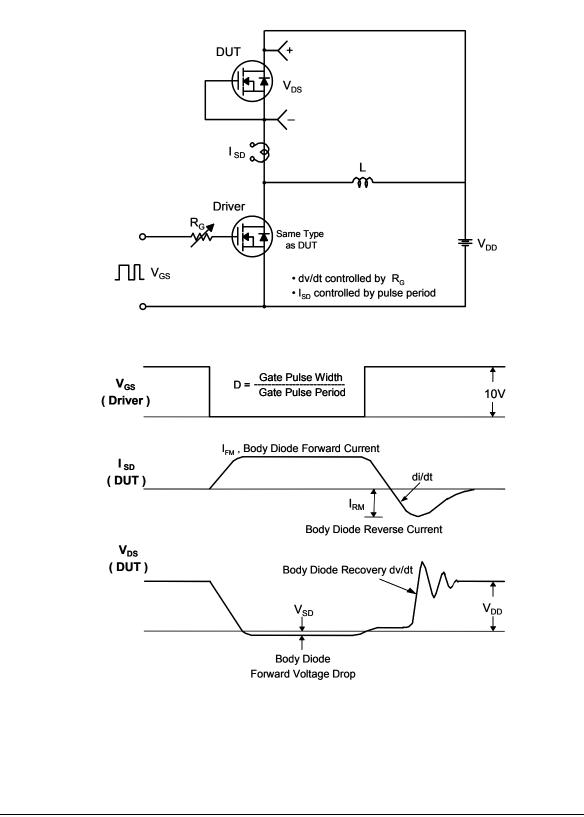






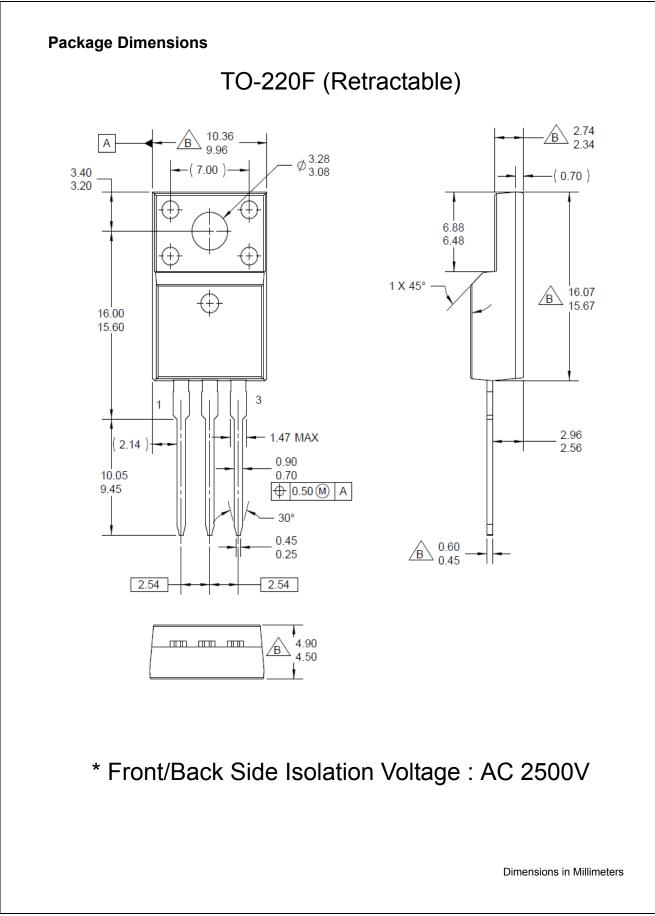


Peak Diode Recovery dv/dt Test Circuit & Waveforms



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Mechanical Dimensions TO-220 ø^{4.09} 3.50∆ ⊕ 0.36 M B AM в 4,83 3,56 А 10.67 9.65 8,89 6,86 'A1' 3.43 2,54 6.86 5.84 ł 7° △13.40 12.19 16.51 △9.40 8.38 1 2 3 3 2 1 ່ 5° 3' 6.35 MAX 5° С ÷ 14.73 12.70 0.61 △0.33 1.78 1.14 (1.91) — 1.02 0,38 2,92 2,03 ⊕ 0.36 [®] B A[®] 2.54 NOTES: UNLESS OTHERWISE SPECIFIED A) REFERENCE JEDEC, TO-220, ISSUE K, VARIATION AB, DATED APRIL, 2002. B) ALL DIMENSIONS ARE IN MILLIMETERS. C) DIMENSIONING AND TOLERANCING PER - 5.08 ANSI Y14.5 - 1973 D) LOCATION OF THE PIN HOLE MAY VARY (LOWER LEFT CORNER, LOWER CENTER 5° 3° 5° 3° AND CENTER OF THE PACKAGE) DOES NOT COMPLY JEDEC STANDARD VALUE, "A1" DIMENSIONS REPRESENT LIKE BELOW: щ mbo SINGLE GAUGE = 0.51 - 0.61 DUAL GAUGE = 1.14 - 1.40 G) DRAWING FILE NAME: TO220B03REV6 **Dimensions in Millimeters**







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